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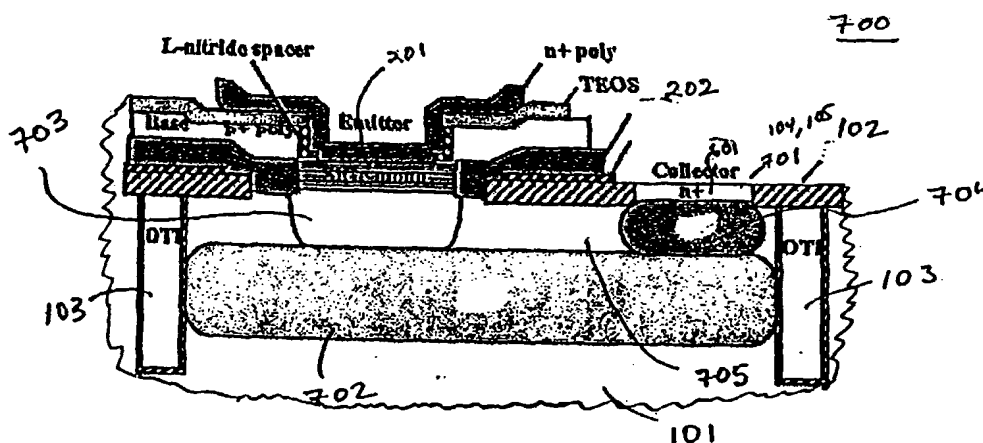
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(54) Title: METHOD OF FABRICATING A SIGE SEMICONDUCTOR STRUCTURE



(57) Abstract: A method of fabricating an integrated circuit includes providing a substrate and creating base-windows in a layer. The method also includes forming a monocrystalline SiGe base layer in each of the base layers, and polycrystalline SiGe elsewhere. Additionally, the method also includes forming a monocrystalline silicon layer over selectively exposed portions of the surface of the substrate. The integrated circuit beneficially includes silicon-based elements such as a lateral pnp transistor, a varactor, and a polysilicon transistor, which are formed on a common substrate with an npn SiGe bipolar transistor.

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